



BSI Standards Publication

Semiconductor devices — Reliability test method for silicon carbide discrete metal-oxide semiconductor field effect transistors

Part 1: Test method for bias temperature instability

National foreword

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The UK participation in its preparation was entrusted to Technical Committee EPL/47, Semiconductors.

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**Semiconductor devices – Reliability test method for silicon carbide discrete metal-oxide semiconductor field effect transistors –
Part 1: Test method for bias temperature instability**

**Dispositifs à semiconducteurs – Méthode d'essai de fiabilité pour les transistors à effet de champ métal-oxyde-semiconducteurs discrets en carbure de silicium –
Partie 1: Méthode d'essai pour la mesure de la dérive de la tension de seuil après polarisation électrique en température**

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INTERNATIONAL ELECTROTECHNICAL COMMISSION

**SEMICONDUCTOR DEVICES –
RELIABILITY TEST METHOD FOR SILICON CARBIDE DISCRETE
METAL-OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTORS –****Part 1: Test method for bias temperature instability****FOREWORD**

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